## NE3516S02

**Data Sheet** 

R09DS0038EJ0100 Rev.1.00 Apr 16, 2012

N-Channel GaAs HJ-FET, X to Ku Band Low Noise and High-Gain

#### **FEATURES**

- Low noise figure and high associated gain NF = 0.35 dB TYP.,  $G_a$  = 14 dB TYP. @ f = 12 GHz,  $V_{DS}$  = 2 V,  $I_D$  = 10 mA NF = 0.35 dB TYP.,  $G_a$  = 13.5 dB TYP. @ f = 12 GHz,  $V_{DS}$  = 2 V,  $I_D$  = 6 mA (Reference Value)
- 4-pin Micro-X plastic (S02) package

### **APPLICATIONS**

- X to Ku band DBS LNB
- Other Ku band communication system

#### ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Marking	Supplying Form
NE3516S02-T1C	NE3516S02-T1C-A	S02	2 kpcs/reel	Р	8 mm wide embossed taping
NE3516S02-T1D	NE3516S02-T1D-A	package (Pb-Free)	10 kpcs/reel		Pin 4 (Gate) faces the perforation side of the tape

Remark To order evaluation samples, please contact your nearby sales office.

Part number for sample order: NE3516S02-A

### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25$ °C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	$V_{DS}$	4.0	V
Gate to Source Voltage	$V_{GS}$	-3.0	V
Drain Current	I <sub>D</sub>	I <sub>DSS</sub>	mA
Gate Current	I <sub>G</sub>	100	μΑ
Total Power Dissipation Note	P <sub>tot</sub>	165	mW
Channel Temperature	T <sub>ch</sub>	+125	°C
Storage Temperature	T <sub>stg</sub>	-65 to +125	°C

Note: Mounted on 1.08 cm<sup>2</sup> × 1.0 mm (t) glass epoxy PWB

### RECOMMENDED OPERATING RANGE ( $T_A = +25$ °C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	$V_{DS}$	+1	+2	+3	V
Drain Current	I <sub>D</sub>	5	10	15	mA
Input Power	Pin	1	1	0	dBm

### **CAUTION**

Observe precautions when handling because these devices are sensitive to electrostatic discharge.





## ELECTRICAL CHARACTERISTICS ( $T_A = +25$ °C, unless otherwise specified)

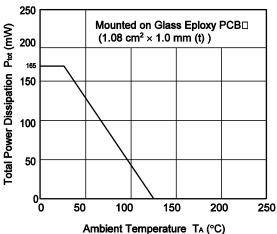
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I <sub>GSO</sub>	$V_{GS} = -3.0 \text{ V}$	-	0.5	10	μА
Saturated Drain Current	I <sub>DSS</sub>	$V_{DS} = 2 \text{ V}, V_{GS} = 0 \text{ V}$	15	30	60	mA
Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = 2V$ , $I_{D} = 100 \mu A$	-0.2	-0.5	-1.3	V
Transconductance	gm	$V_{DS} = 2 \text{ V}, I_{D} = 10 \text{ mA}$	55	65	_	mS
Noise Figure	NF	$V_{DS} = 2 \text{ V}, I_D = 10 \text{ mA}, f = 12 \text{ GHz}$	_	0.35	0.50	dB
Associated Gain	Ga	]	13	14	_	dB

# STANDARD CHARACTERISTICS FOR REFERENCE $(T_A = +25^{\circ}C, unless otherwise specified)$

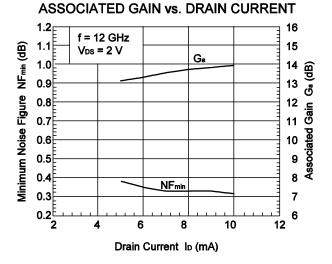
Parameter	Symbol	Test Conditions	Reference Value	Unit
Noise Figure	NF	$V_{DS} = 2 \text{ V}, I_D = 6 \text{ mA}, f = 12 \text{ GHz}$	0.35	dB
Associated Gain	Ga		13.5	dB

## TYPICAL CHARACTERISTICS ( $T_A = +25$ °C, unless otherwise specified)



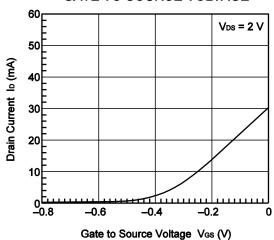


# MINIMUM NOISE FIGURE,

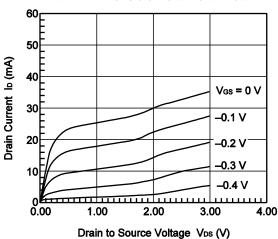


#### Remark The graph indicates nominal characteristics.

## DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



## DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE





### **S-PARAMETERS**

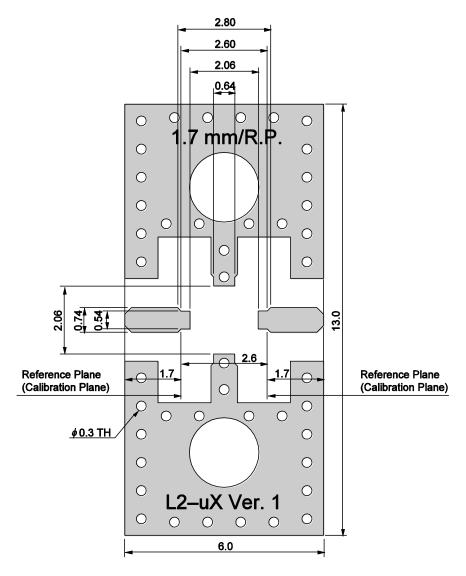
	S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import to
mi	icrowave circuit simulators without keyboard inputs.
	Click here to download S-parameters.

 $\ \, \square \ \, [\mathsf{Products}] \to [\mathsf{RF} \ \mathsf{Devices}] \to [\mathsf{Device} \ \mathsf{Parameters}]$ 

 $\ \ \Box \ \ URL \ \ http://www.renesas.com/products/microwave/download/parameter/$ 



### RF MEASURING LAYOUT PATTERN (REFERENCE ONLY) (UNIT: mm)



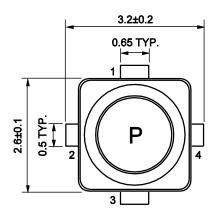
RT/duroid 5880/ROGERS t = 0.254 mm εr = 2.20 tan delta = 0.0009 @10 GHz



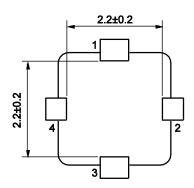
## **PACKAGE DIMENSIONS**

### S02 (UNIT: mm)

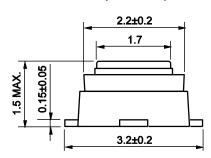
## (Top View)



### (Bottom View)



### (Side View)



### **PIN CONNECTIONS**

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate



### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature)	: 260°C or below	IR260
	Time at peak temperature	: 10 seconds or less	
	Time at temperature of 220°C or higher	: 60 seconds or less	
	Preheating time at 120 to 180°C	: 120±30 seconds	
	Maximum number of reflow processes	: 3 times	
	Maximum chlorine content of rosin flux (% mass)	: 0.2% (Wt.) or below	
Partial Heating	Peak temperature (terminal temperature)	: 350°C or below	HS350
	Soldering time (per side of device)	: 3 seconds or less	
	Maximum chlorine content of rosin flux (% mass)	: 0.2% (Wt.) or below	

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Do not use different soldering methods together (except for partial heating).

Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
  - Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
- 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.

**Revision History** 

## NE3516S02 Data Sheet

			Description		
Rev.	Date	Page	Summary		
1.00	Apr 16, 2012	_	First edition issued		